SILICON PNP TRANSISTOR
EPITAXIAL PLANAR TYPE (PCT PROCESS)

2SA1270

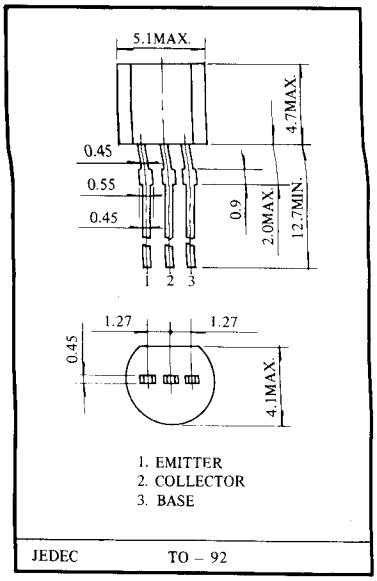
APPLICATIONS

- Low Frequency, Low Power Amplifiers
- General-driver Stage Amplifiers
- General Purpose Switching Applications

FEATURES

- Excellent h_{FE} vs. Collector Current Characteristics, $h_{FE}(2)$ =25min. at V_{CE}=−6V, Ic=−400mA
- Ic=max.=−500mA
- Pc max.=500mW
- Complementary to the 2SC 3202

Unit in mm



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC TO−92

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector−Base Voltage	V_{CBO}	−35	V
Collector−Emitter Voltage	V_{CEO}	−30	V
Emitter−Base Voltage	V_{EBO}	−5	V
Collector Current	I_C	−500	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Emitter Current	I_E	500	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	−55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut off Current	I_{CBO}	V_{CB}=−35V, I_E=0	−	−	−0.1	μA
Emitter Cut off Current	I_{EBO}	V_{EB}=−5V, I_C=0	−	−	−0.1	μA
DC Current Gain(1)	$h_{FE(1)}$	V_{CE}=−1V, I_C=−100mA	70	−	240	
DC Current Gain(2)	$h_{FE(2)}$ (Pulsed)	V_{CE}=−6V, I_C=−400mA	25	−	−	
Collector−Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=−100mA, I_B=−10mA	−	−0.1	−0.25	V
Base−Emitter Voltage	V_{BE}	I_C=−100mA, V_{CE}=−1V	−	−0.8	−1.0	V
Transition Frequency	f_T	V_{CE}=−6V, I_E=20mA	−	200	−	MHz
Output Capacitance	C_{ob}	V_{CB}=−6V, I_E=0, f=1MHz	−	13	−	pF

Note : According to h_{FE}(1) Classified as follows

O	70~140	Y	120~240

KEC